

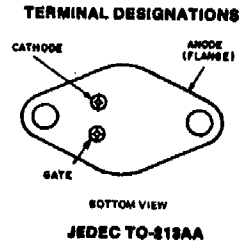
S3700 Series

5-A Silicon Controlled Rectifiers

For Inverter Applications

Features:

- 600V, 125°C T_J operating
- High dv/dt and di/dt capability
- Low switching losses
- High pulse-current capability
- Low forward and reverse leakage
- SIPOS oxide glass multilayer passivation system
- Advanced unisurface construction
- Precise ion-implanted diffusion source



MAXIMUM RATINGS, Absolute-Maximum Values:

	S3700B	S3700D	S3700M	
Non-repetitive peak reverse voltage:■				
Gate Open V _{RR0M}	300	500	700	V
Non-repetitive peak off-state voltage:■				
Gate Open V _{RO0M}	300	500	700	V
Repetitive peak reverse voltage:■				
Gate Open V _{RR0M}	200	400	600	V
Repetitive peak off-state voltage:■				
Gate Open V _{RO0M}	200	400	600	V
On-state current:				
T _c = 85°C; conduction angle = 180°:				
RMS I _{TRMS}		5		A
Average I _{TAVM}		3.2		A
For other conditions		See Figs. 3 & 4		
Peak surge (non-repetitive) on-state current:				
For one full cycle of applied principal voltage, T _c = 85°C				
60 Hz (sinusoidal) I _{TRM}		80		A
50 Hz (sinusoidal) I _{TRM}		65		A
For more than one full cycle of applied principal voltage		See Fig. 5		
Rate of change of on-state current				
V ₀ = V _{RR0M} , I _{GT} = 50 mA, t _r = 0.1 μs di/dt		200		A/μs
Fusing current (for SCR protection):				
T _J = -40 to 100°C, t = 1 to 8.3 ms I _{FT}		25		A
Gate power dissipation:†				
Peak Forward (for 10 μs max., See Fig. 7) P _{GM}		13		W
Peak Reverse (for 10 μs max., See Fig. 8) P _{GRM}		13		W
Average (averaging time = 10 ms max.) P _{GIAM}		0.5		W
Temperature Range:†				
Storage T _{stg}		-40 to 150		°C
Operating (Case) T _c		-40 to 125		°C
Pin Temperature (During soldering):				
At distances ≥ 1/32 in. (0.8 mm) from seating plane for 10 s max. T _p		225		°C

■ These values do not apply if there is a positive gate signal. Gate must be open or negatively biased.
 * Any product of gate current and gate voltage which results in a gate power less than the maximum is permitted.
 † For temperature measurement reference point, see *Dimensional Outline*.



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S3700 Series

ELECTRICAL CHARACTERISTICS

At Maximum Ratings Unless Otherwise Specified and at Indicated Case Temperature (T_C)

CHARACTERISTIC	SYMBOL	LIMITS			UNITS
		FOR ALL TYPES Except as Specified			
		MIN.	TYP.	MAX.	
Peak Off-State Current: (Gate open, $T_C = 125^\circ\text{C}$) Forward Current (I_{DOM}) at $V_D = V_{DROM}$	I_{DOM}	—	0.5	3	mA
Reverse Current (I_{ROM}) at $V_R = V_{RROM}$	I_{ROM}	—	0.3	1.5	
Instantaneous On-State Voltage: $i_T = 30\text{ A (peak)}$, $T_C = 25^\circ\text{C}$	v_T	—	2.2	3	V
For other conditions			See Fig. 6		
Instantaneous Holding Current: Gate open, $T_C = 25^\circ\text{C}$	i_{HO}	—	20	50	mA
Critical Rate of Rise of Off-State Voltage: $V_D = V_{DROM}$, exponential voltage rise, Gate open, $T_C = 125^\circ\text{C}$	dv/dt	100	250	—	V/ μs
DC Gate Trigger Current: $V_D = 12\text{ V (dc)}$, $R_L = 30\ \Omega$, $T_C = 25^\circ\text{C}$	I_{GT}	—	15	40	mA
For other conditions			See Fig. 7		
DC Gate Trigger Voltage: $V_D = 12\text{ V (dc)}$, $R_L = 30\ \Omega$, $T_C = 25^\circ\text{C}$	V_{GT}	—	1.8	3.5	V
For other conditions			See Fig. 7		
Gate Controlled Turn-On Time: (Delay Time + Rise Time) For $V_{DX} = V_{DROM}$, $I_{GT} = 300\text{ mA}$, $t_r = 0.1\ \mu\text{s}$, $i_T = 2\text{ A (peak)}$, $T_C = 25^\circ\text{C}$ (See Fig. 10)	t_{gt}	—	0.7	—	μs
Circuit Commutated Turn-Off Time: $V_{DX} = V_{DROM}$, $i_T = 2\text{ A}$, pulse duration = $50\ \mu\text{s}$, $dv/dt = 100\text{ V}/\mu\text{s}$, $-di/dt = -10\text{ A}/\mu\text{s}$, $I_{GT} = 100\text{ mA}$, $V_{GT} = 0\text{ V}$ (at turn-off), $T_C = 80^\circ\text{C}$ (See Fig. 13)	t_q	—	4	6	μs
Thermal Resistance: Junction-to-Case	$R_{\theta JC}$	—	4	8	$^\circ\text{C}/\text{W}$
Junction-to-Ambient	$R_{\theta JA}$	—	—	40	$^\circ\text{C}/\text{W}$

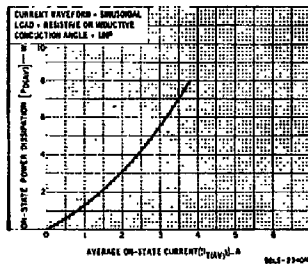


Fig. 1—Power dissipation vs. average on-state current.

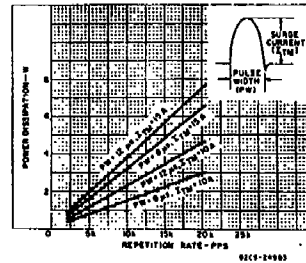


Fig. 2—Dissipation vs. repetition rate.